Silicon NPN Power Transistors 2SC1185

DESCRIPTION

- ·With TO-3 package
- ·Wide area of safe operation
- ·High breakdown voltage
  :V_{CEO}=250V(min)

APPLICATIONS

- ·For voltage regulator,inverter,switching mode power supply applications.

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

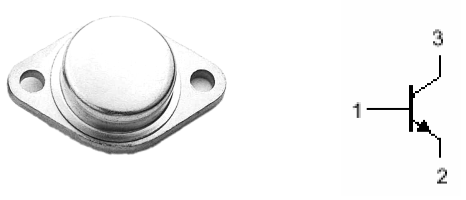

Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=?)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	300	V
V_{CEO}	Collector-emitter voltage	Open base	250	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		0.7	A
P_D	Total power dissipation	T_C=25?	50	W
T_j	Junction temperature		150	?
T_{stg}	Storage temperature		-55~150	?

CHARACTERISTICS

Tj=25? unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=30mA; I_B=0	250			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=1mA; I_E=0	300			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=1mA; I_C=0	5			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=500mA; I_B=100mA			1.0	V
V_{BEsat}	Base-emitter saturation voltage	I_C=500mA; I_B=100mA			1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=200V;I_E=0			10	µA
I_{EBO}	Emitter cut-off current	V_{EB}=5V; I_C=0			10	µA
h_{FE}	DC current gain	I_C=0.4A ; V_{CE}=10V	40		200	

PACKAGE OUTLINE

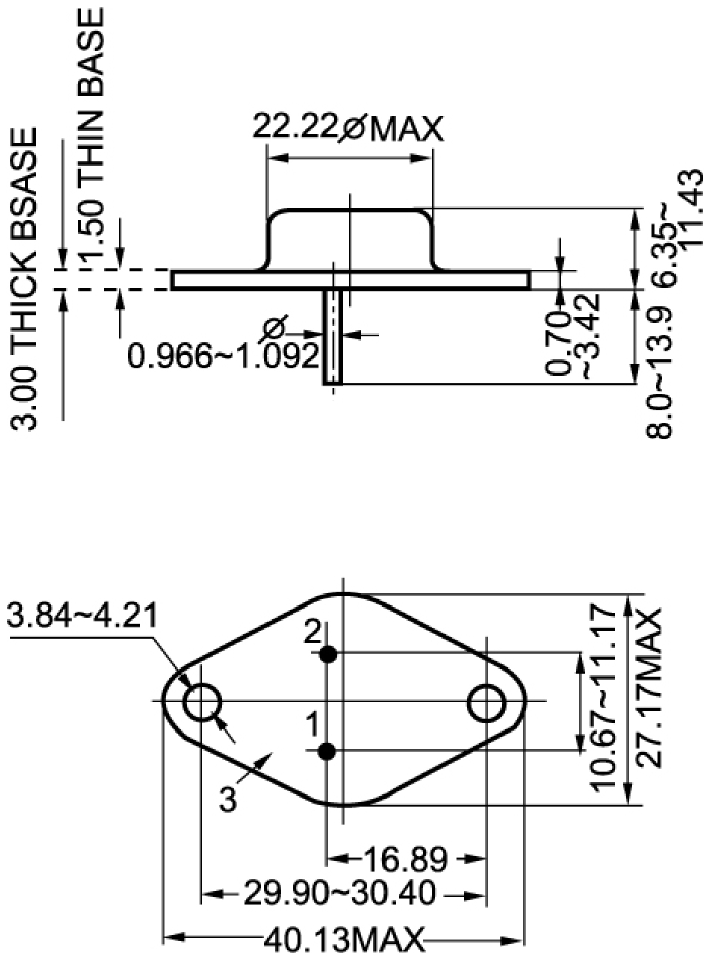

Fig.2 outline dimensions